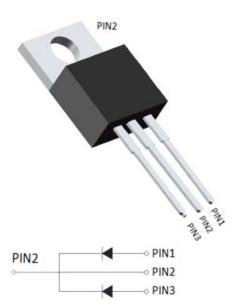


Schottky Diodes



Features

- High frequency operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

• Package: TO-220AB

Molding compound meets UL 94 V-0 flammability

rating, RoHS-compliant

• **Terminals**: Tin plated leads, solderable per J-STD-

002 and JESD22-B102

• Polarity: As marked

■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBR10200CT
Device marking code			MBR10200CT
Repetitive Peak Reverse Voltage	VRRM	V	200
Average Rectified Output Current @60Hz sine wave, R-load, Ta=25°C	Ю	Α	10
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, T _a =25℃	IFSM	Α	100
Current Squared Time @1ms≤t≤8.3ms Tj=25℃	l²t	A ² s	41
Storage Temperature	Tstg	$^{\circ}$	-55 ~ +175
Junction Temperature	Тј	$^{\circ}$	-55 ~ + 175

■Electrical Characteristics (T_a=25 °C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBR10200CT
Maximum instantaneous forward voltage drop per diode	VFM	V	IFM=5.0A	0.95
Maximum DC reverse current	IRRM1	mA	VRM=VRRM T _a =25°C	0.1
at rated DC blocking voltage per diode	IRRM2		VRM=VRRM T _a =100°C	20

Note1:Pulse test:300uS pulse widh,1% duty cycle

Note2:Pulse test:pulse widh 40mS

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARA	AMETER	SYMBOL	UNIT	MBR10200CT
Thermal Resistance	Between junction and case	R _{θJ-C}	°CMV	2.0

■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBR10200CT	Approximate 1.9	50	1000	5000	Tube

■Characteristics (Typical)

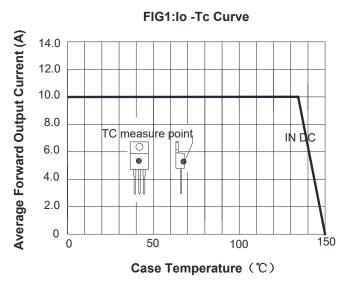
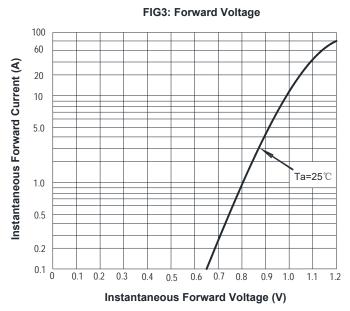
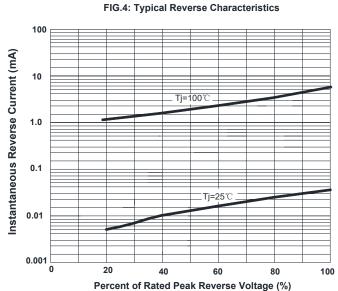


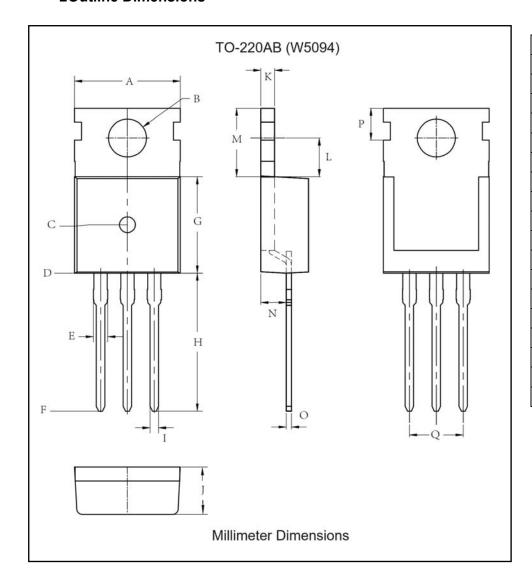
FIG2:Surge Forward Current Capability 140 Peak Forward Surge Current (A) 120 100 8.3ms Single Half Sine-Wave 80 JEDEC Method 60 40 20 2 5 10 20 50 100 **Number of Cycles**







■Outline Dimensions



TO-220AB							
Dim	Min	Max					
Α	9.9	10.1					
В	TYP 3.6						
С	8.06	8.46					
D	12.67	13.07					
Е	1.28	1.42					
F	25.7	26.3					
G	9	9.4					
Н	12.93	13.33					
1	TYP 0.8						
J	4.3	4.7					
K	1.285	1.315					
L	3.47	3.87					
М	6.27	6.67					
Ν	2.2	2.6					
0	0.485	0.515					
Р	2.8	3.2					
Q	TYP 5.08						



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